N-channel TrenchMOS standard level FET

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

Low conduction losses due to low on-state resistance

3. Applications

- DC-to-DC convertors switching
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	150	V	
I _D	drain current	T _{sp} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>		-	-	5	Α	
P _{tot} total power dissipation T _{sp} = 25 °C; <u>Fig. 2</u>		T _{sp} = 25 °C; <u>Fig. 2</u>		-	-	6.25	W	
Static characteristics							•	
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10		-	56	75	mΩ	
Dynamic chara	Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 75 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 11$		-	12	-	nC	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	8 <u>月 月 月 月</u> 5	D I
2	S	source		
3	S	source		G—U: 4
4	G	gate	1 1 1 1 1 1 1 1	mbb076 S
5	D	drain	SO8 (SOT96-1)	
6	D	drain		
7	D	drain		
8	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHK5NQ15T	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1			

7. Marking

Table 4. Marking codes

•	
Type number	Marking code
PHK5NQ15T	K5NQ15T

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	150	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 150$ °C; $R_{GS} = 20$ kΩ	-	150	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{sp} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	3.23	Α
		T _{sp} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>	-	5	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	20	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 2</u>	-	6.25	W

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Symbol	Parameter	Conditions		Min	Max	Unit		
T _{stg}	storage temperature			-55	150	°C		
Tj	junction temperature			-55	150	°C		
Source-drain diode								
I _S	source current	T _{sp} = 25 °C		-	5	Α		
I _{SM}	peak source current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$		-	20	Α		

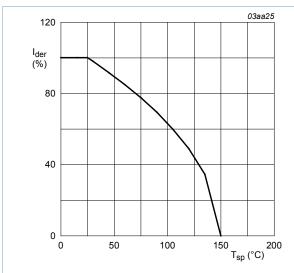


Fig. 1. Normalized continuous drain current as a function of solder point temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

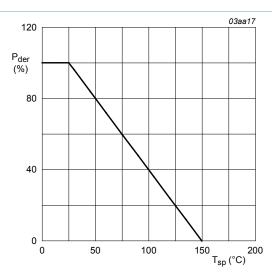


Fig. 2. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

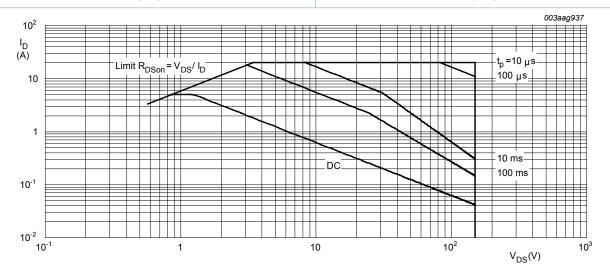


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25^{\circ}C$$
; I_{DM} is a single pulse

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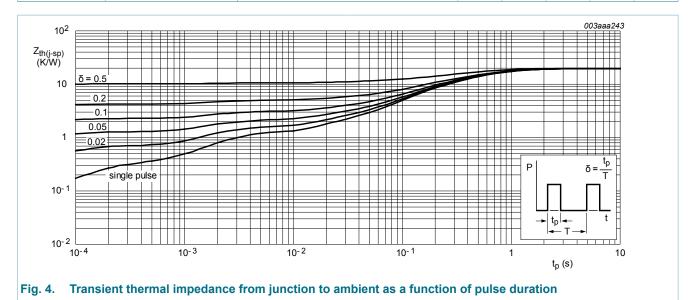
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	Fig. 4	-	-	20	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on printed-circuit board	-	70	-	K/W



10. Characteristics

Table 7. Characteristics

ristics drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ $I_D = 250 \mu A; V_{GS} = 0 V; T_i = 25 °C$	134	-	-	V
	- , 5, ,	134	-	_	V
breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C				V
	,	150	-	-	V
gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 8	-	-	4.5	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ Fig. 8	1.2	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 8$	2	3	4	V
drain leakage current	V _{DS} = 120 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
	V _{DS} = 120 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μΑ
gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
(drain leakage current	$I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 150 \text{ °C;}$ $Fig. 8$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } Fig. 8$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 150 \text{ °C}$	$I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 150 \text{ °C;}$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } Fig. 8$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } Fig. 8$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 150 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ - gate leakage current $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ -	$I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 150 \text{ °C;}$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } \underline{Fig. 8}$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } \underline{Fig. 8}$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 150 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$	$I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 150 \text{ °C;}$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } \underline{Fig. 8}$ $I_{D} = 1 \text{ mA; } V_{DS} = V_{GS}; T_{j} = 25 \text{ °C; } \underline{Fig. 8}$ $2 \qquad 3 \qquad 4$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{DS} = 120 \text{ V; } V_{GS} = 0 \text{ V; } T_{j} = 150 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$ $V_{GS} = 10 \text{ V; } V_{DS} = 0 \text{ V; } T_{j} = 25 \text{ °C}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 150 °C;$ Fig. 9; Fig. 10	-	129	173	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	60	80	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9;$ Fig. 10	-	56	75	mΩ
R_G	gate resistance	f = 1 MHz	-	1.9	3.8	Ω
Dynamic cl	haracteristics		<u> </u>			
Q _{G(tot)}	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 75 \text{ V}; V_{GS} = 10 \text{ V};$	-	29	41	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 11</u>	-	3	-	nC
Q_{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	1150	1553	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 12</u>	-	187	252	pF
C _{rss}	reverse transfer capacitance		-	61	85	pF
t _{d(on)}	turn-on delay time	V_{DS} = 75 V; R_L = 15 Ω ; V_{GS} = 10 V;	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C; I_D = 5 A$	-	12	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	18	-	ns
Source-dra	in diode		l			
V _{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 13$	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	87	113	ns
Q _r	recovered charge	V _{DS} = 90 V; T _j = 25 °C	-	162	-	nC

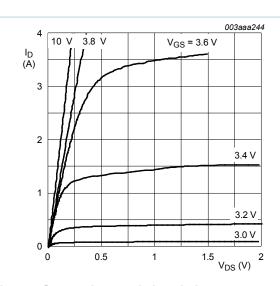


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



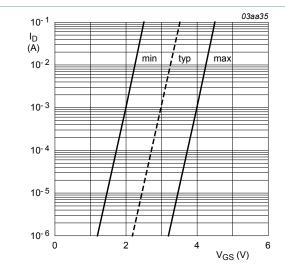


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j=25\,^{\circ}C; V_{DS}=5V$$

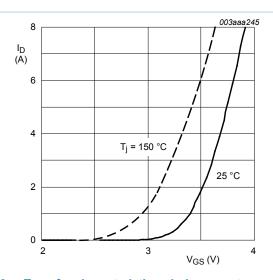


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$T_j = 25$$
°C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

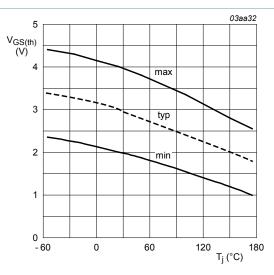


Fig. 8. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

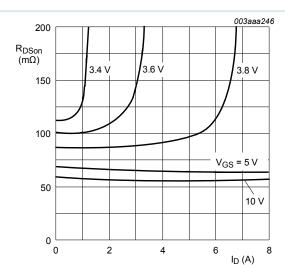


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

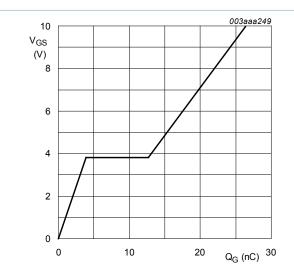


Fig. 11. Gate-source voltage as a function of gate charge; typical values

$$I_D = 5A; V_{DD} = 75V$$

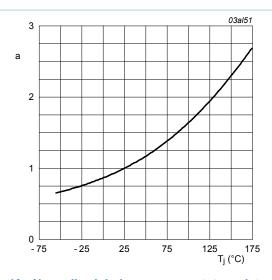


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

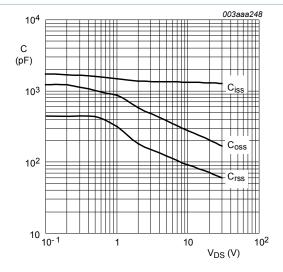


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

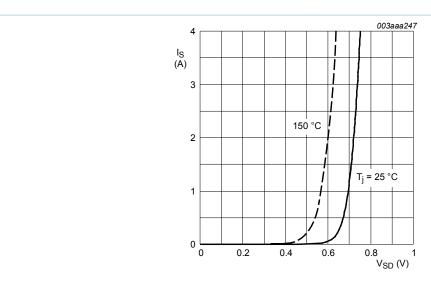
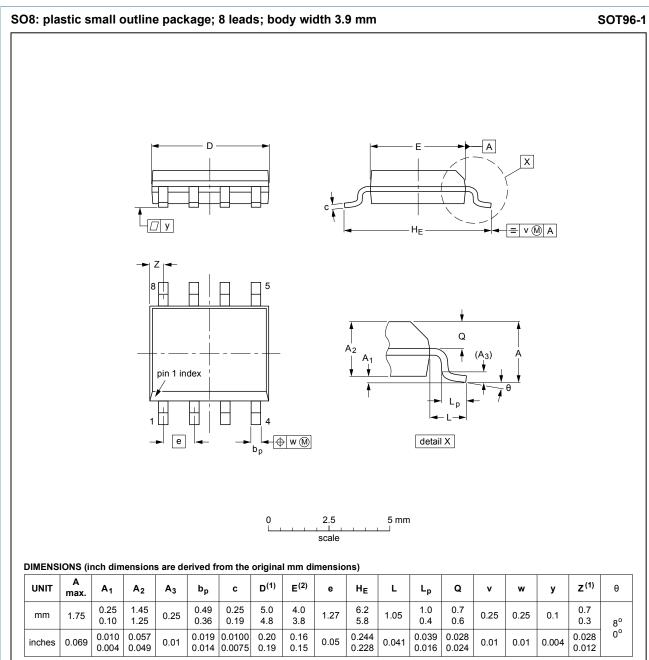


Fig. 13. Source current as a function of source-drain voltage; typical values

$$T_j = 25$$
° C and 150 ° C ; $V_{GS} = 0V$

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11. Package outline



...

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012			99-12-27 03-02-18

Fig. 14. Package outline SO8 (SOT96-1)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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